

## TO-251 Plastic-Encapsulate Transistors

ALJ13003

TRANSISTOR(NPN)

### FEATURES

Power dissipation

PCM:1.25W(Tamb=25°C)

Collector current

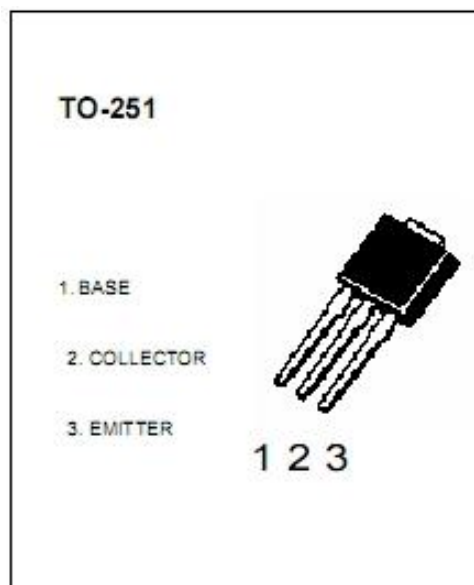
ICM:1.2A

Collector-base voltage

V(BR)CBO: 600V

Operating and storage junction temperature range

TJ,Tstg:-65°C to -150°C



ELECTRICAL CHARACTERISTICS(Tamb=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) <sub>CBO</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0	600			V
Collector-emitter breakdown voltage	V(BR) <sub>CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	400			V
Emitter-base breakdown voltage	V(BR) <sub>EBO</sub>	I <sub>C</sub> =1mA, I <sub>C</sub> =0	9			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =600V, I <sub>E</sub> =0			0.5	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =400V, I <sub>B</sub> =0			1.0	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =9V, I <sub>C</sub> =0			0.1	μA
DC current gain	H <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	10		40	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =0.5A, I <sub>B</sub> =0.1A			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =0.5A, I <sub>B</sub> =0.1A			1.2	V
Storage time	t <sub>s</sub>	V <sub>CC</sub> =5V I <sub>C</sub> =0.25A (UI9600)	2.0		4.0	μs
Falling Time	t <sub>f</sub>				1.0	μs